



DMN4031SSDQ

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C (Note 6)
401/	31mΩ @ V _{GS} = 10V	7.0A
40V	$50m\Omega @ V_{GS} = 4.5V$	5.8A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

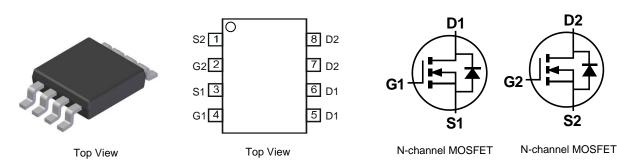
- Low On-Resistance
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN4031SSDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

SO-8



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4031SSDQ-13	SO-8	2,500/Tape & Reel

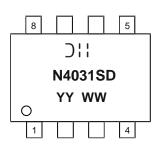
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



)|| = Manufacturer's Marking N4031SD = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 21 = 2021) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Ch	Symbol	Value	Unit			
Drain-Source Voltage	V _{DSS}	40	V			
Gate-Source Voltage				Vgss	±20	V
Continuous Drain Current (Note 5)	VGS = 10V	Steady State	T _A = +25°C T _A = +70°C	lD	5.2 4.1	A
Continuous Drain Current (Note 5)	$V_{GS} = 4.5V$	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	4.3 3.4	А
Continuous Drain Current (Note 6)	V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	lo	7.0 5.6	A
Continuous Drain Current (Note 6)	V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	lD	5.8 4.7	A
Pulsed Drain Current (Note 7)				I _{DM}	40	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	1.42	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	Reja	88	°C/W
Total Power Dissipation (Note 6)	PD	2.6	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	Reja	48	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

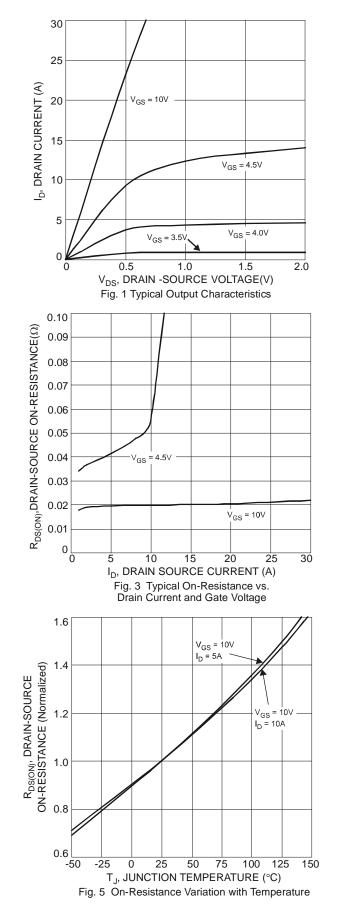
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Cymbol		i yp	Mux	Unit		
Drain-Source Breakdown Voltage	BVDSS	40	_	_	V	$V_{GS} = 0V, I_{D} = 10mA$	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•						
Gate Threshold Voltage	Vgs(th)	1.6	2.4	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
On-State Drain Current	ID(ON)	20	_	_	А	Vgs = 10V, Vds = 5A	
Static Drain-Source On-Resistance	Descent	_	19	31	mΩ	VGS = 10V, ID = 6A	
Static Drain-Source On-Resistance	Rds(on)	_	44	50		V _{GS} = 4.5V, I _D = 5A	
Forward Transfer Admittance	Y _{fs}	_	11	_	S	$V_{DS} = 5V, I_D = 6A$	
Diode Forward Voltage	Vsd	_	0.74	1.0	V	VGS = 0V, IS = 1A	
DYNAMIC CHARACTERISTICS (Note 9)						-	
Input Capacitance	Ciss	_	945	—	pF		
Output Capacitance	Coss	_	69	—	pF	$V_{DS} = 20V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	58	_	pF	1 = 1.00012	
Gate Resistance	Rg	_	1.45	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge ($V_{GS} = 4.5V$)	Qg		8.4	-	nC	$V_{GS} = 4.5V, V_{DS} = 20V,$ $I_{D} = 12A$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	18.6	_	nC		
Gate-Source Charge	Q _{gs}	_	3.3	_	nC	$V_{GS} = 10V, V_{DS} = 20V, I_D = 12A$	
Gate-Drain Charge	Qgd	_	2.2	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	6.4	_	ns		
Turn-On Rise Time	tR	_	9.7	—	ns	Vgs = 10V, Vds = 20V,	
Turn-Off Delay Time	tD(OFF)	_	19.8	_	ns	R _L = 1.6Ω, R _G = 3Ω	
Turn-Off Fall Time	tF		3.1	_	ns		

 Device mounted on FR-4 PCB, with minimum recommended pad layout. The value in any given application depends on user's specific board design.
Device mounted on 1" x 1" FR-4 PCB with high coverage 1 oz. Copper, single sided.
Repetitive rating, pulse width limited by junction temperature. Notes:

8. Short duration pulse test used to minimize self-heating effect

9. Guaranteed by design. No subject to production testing.





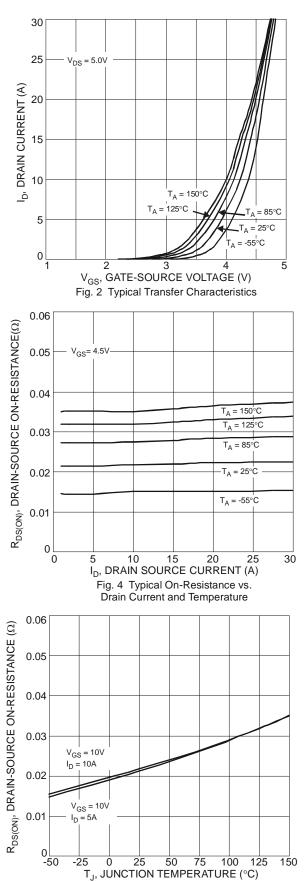
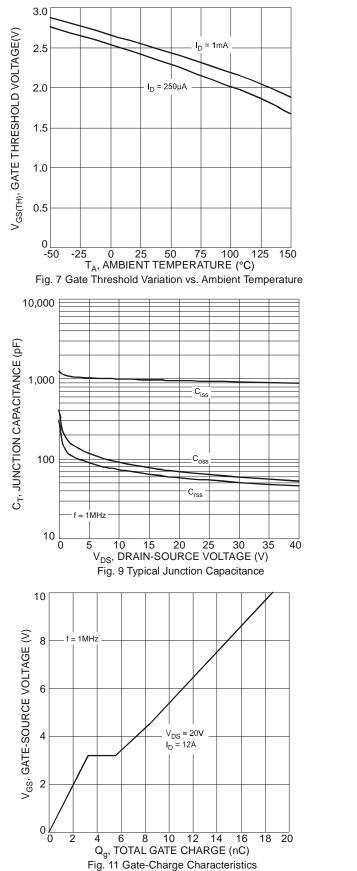
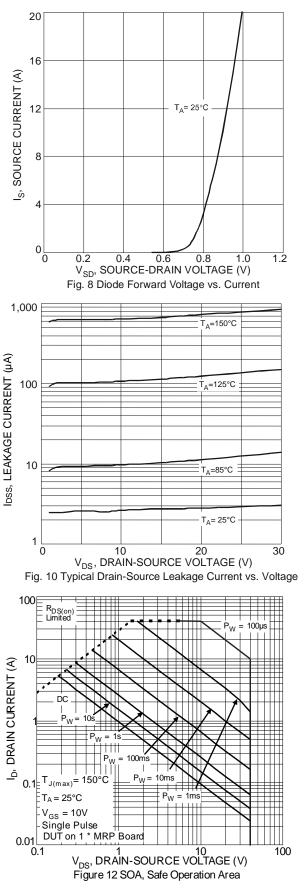


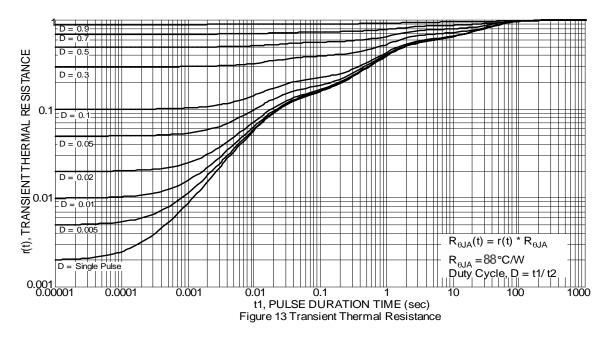
Fig. 6 On-Resistance Variation with Temperature







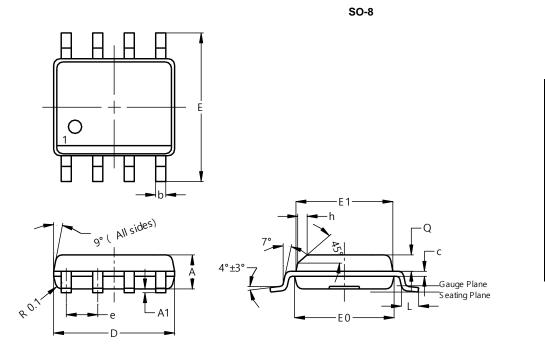






Package Outline Dimensions

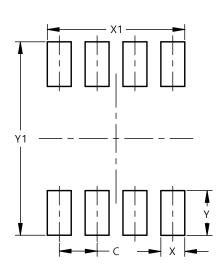
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8						
Dim	Min	Max	Тур			
Α	1.40	1.50	1.45			
A1	0.10	0.20	0.15			
b	0.30	0.50	0.40			
с	0.15	0.25	0.20			
D	4.85	4.95	4.90			
ш	5.90	6.10	6.00			
E1	3.80	3.90	3.85			
E0	3.85	3.95	3.90			
e		-	1.27			
h			0.35			
1	0.62	0.82	0.72			
Q	0.60	0.70	0.65			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50

SO-8



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